

A B S T R A C T

A semiconductor laser includes a substrate made of InP, an active layer including a multiquantum well structure, which is formed in a width of 7 to 14 μm on the substrate, and an n-type cladding layer made of InGaAsP and a p-type cladding layer made of InP, which are formed on the substrate with the active layer interposed therebetween. The semiconductor laser oscillates only in the fundamental lateral mode, and light emitted from an exit facet can be optically coupled with an external single mode optical fiber.